

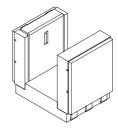
Subminiature Dual Channel Transmissiv Sensor with Phototransistor Output

Description

TCPT1300X01, a transmissive optical sensor SMD including an IR emitter and a Phototransistor detector located face to face with 3 mm gap and 0.3 mm aperture dimension. The operating wavelength is 950 nm.

Features

- IR Emitter wavelength 950 nm
- Aperture 0.3 mm
- Gap 3 mm
- · Package height: 4 mm
- Surface Mountable Device (SMD)
- Parts shipped taped and reeled 2000 pcs/ reel
- Option X01: High reliability device for advanced applications
- Lead (Pb)-free component in accordance with-RoHS 2002/95/EC and WEEE 2002/96/EC



19601

Applications

Accurate position sensor for encoder

Detection of motion speed

Detection of motor speed and direction where high reliability performance is required

Parts Table

Part	Resolution	Aperture	MOQ	Remarks
TCPT1300X01	0.24 mm	0.3 mm	2000 pcs	Tape and Reel

Absolute Maximum Ratings

Coupler

Parameter	Test condition	Symbol	Value	Unit
Total power dissipation	T _{amb} ≤ 25 °C	P _{tot}	150	mW
Ambient temperature range		T _{amb}	- 40 to + 85	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	in accordance to released reflow solder profile	T _{sd}	260	°C

Input (Emitter)

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_{R}	5	V
Forward current		Ι _F	25	mA
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	100	mA
Power dissipation	T _{amb} ≤ 25 °C	P _V	75	mW

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TCPT1300X01

Vishay Semiconductors



Output (Detector)

Parameter	Test condition	Symbol	Value	Unit
Collector emitter voltage		V _{CEO}	70	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		I _C	20	mA
Power dissipation	T _{amb} ≤ 25 °C	P _V	75	mW

Electrical Characteristics

Coupler

 T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Collector current per channel	$V_{CE} = 5 \text{ V}, I_F = 15 \text{ mA}$	I _C	300	500		μΑ
Collector emitter saturation voltage	$I_F = 15 \text{ mA}, I_C = 0.05 \text{ mA}$	V _{CEsat}			0.4	V

Input (Emitter)

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Forward voltage	I _F = 15 mA	V _F		1.2	1.5	V
Reverse current	V _R = 5 V	I _R			10	μΑ
Junction capacitance	V _R = 0 V, f = 1 MHz	C _j		50		pF

Output (Detector)

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Collector emitter voltage	I _C = 1 mA	V_{CEO}	70			V
Emitter collector voltage	I _E = 100 μA	V _{ECO}	7			V
Collector-emitter cut-off current	$V_{CE} = 25 \text{ V}, I_F = 0, E = 0$	I _{CEO}		10	100	nA

Switching Characteristics

 T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Rise time	I_C = 0.3 mA, V_{CE} = 5 V, R_L = 1000 Ω (see figure 2)	t _r		20.0	150	μs
Fall time	I_C = 0.3 mA, V_{CE} = 5 V, R_L = 1000 Ω (see figure 2)	t _f		30.0	150	μS



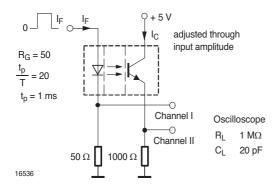


Figure 1. Test Circuit for t_r and t_f

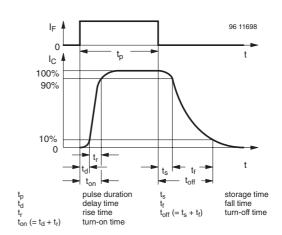


Figure 2. Pulse Diagram

Typical Characteristics

 T_{amb} = 25 °C, unless otherwise specified

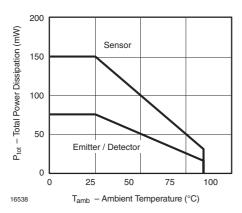


Figure 3. Derating Diagram

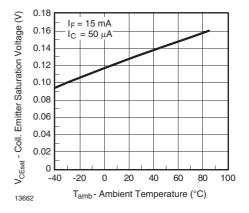


Figure 5. Collector Emitter Saturation Voltage vs. Ambient Temperature

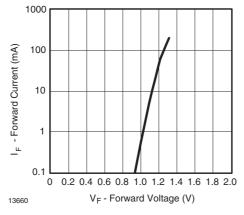


Figure 4. Forward Current vs. Forward Voltage

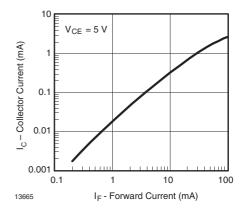


Figure 6. Collector Current vs. Forward Current



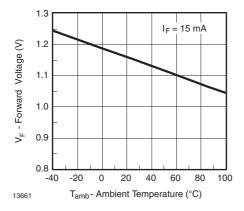


Figure 7. Forward Voltage vs. Ambient Temperature

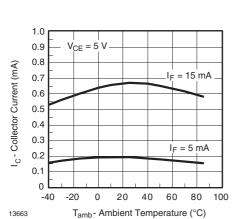


Figure 8. Collector Current vs. Ambient Temperature

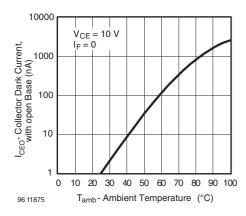


Figure 9. Collector Dark Current vs. Ambient Temperature

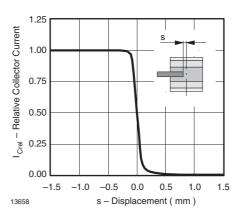


Figure 10. Relative Collector Current vs. Displacement

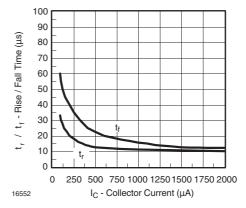


Figure 11. Rise/ Fall Time vs. Collector Current

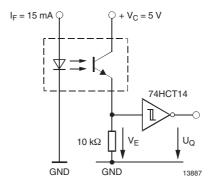


Figure 12. Application example



Reflow Solder Profiles

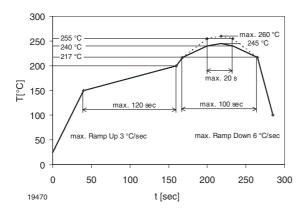


Figure 13. Lead-Free (Sn) Reflow Solder Profile

Drypack

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

Floor Life

Acc. JEDEC, J-STD-020, Level 2, floor life must not exceed 12 month (time between soldering and removing from MBB), with Floor Conditions: $T_{amb} < 30 \,^{\circ}\text{C}$, RH < 60 %.

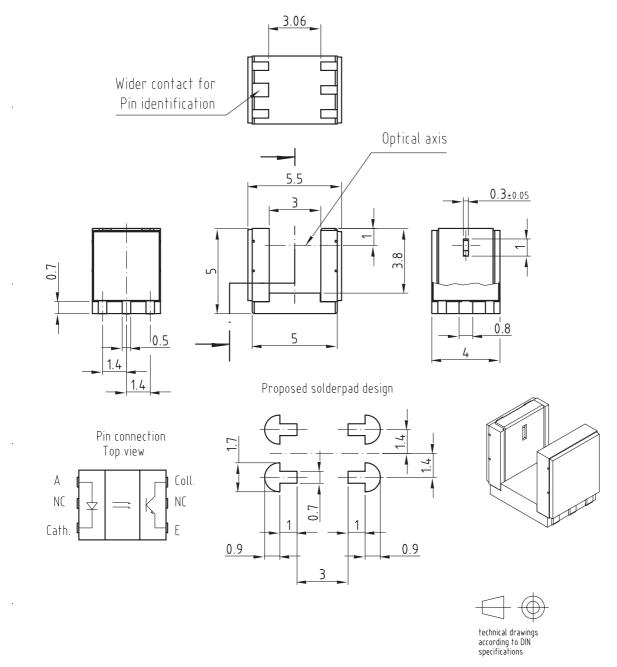
Drying

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or Label. Devices taped on reel dry using recommended conditions 192 h @ 40 °C (\pm 5 °C), RH < 5 % or 96 h @ 60 °C (\pm 5 °C), RH < 5 %

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Package Dimensions in mm



Drawing refers to following types: TCPT 1300

Drawing-No.: 6.541-5062.01-4

Issue: 1; 18.08.05

All dimensions in mm incl. burrs Not indicated tolerances ±0.15

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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

> We reserve the right to make changes to improve technical design and may do so without further notice.

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